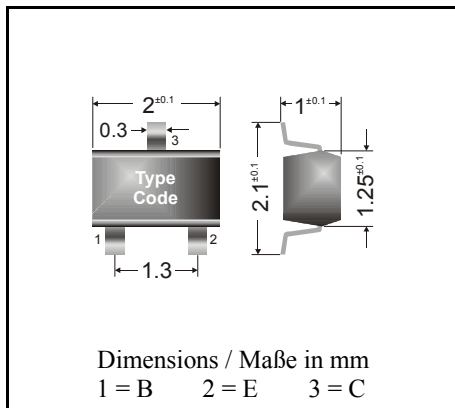


PNP

Surface mount Si-Epitaxial Planar Transistors
Si-Epitaxial Planar Transistoren für die Oberflächenmontage

PNP



Power dissipation – Verlustleistung	225 mW
Plastic case Kunststoffgehäuse	SOT-323
Weight approx. – Gewicht ca.	0.01 g
Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert	
Standard packaging taped and reeled Standard Lieferform gegurtet auf Rolle	

Maximum ratings (T_A = 25°C)**Grenzwerte (T_A = 25°C)**

			BC 807W	BC 808W
Collector-Emitter-voltage	B open	- V _{CE0}	45 V	25 V
Collector-Emitter-voltage	B shorted	- V _{CES}	50 V	30 V
Collector-Base-voltage	E open	- V _{CB0}	50 V	30 V
Emitter-Base-voltage	C open	- V _{EB0}	5 V	
Power dissipation – Verlustleistung		P _{tot}	225 mW ¹⁾	
Collector current – Kollektorstrom (DC)		- I _C	500 mA	
Peak Coll. current – Kollektor-Spitzenstrom		- I _{CM}	1000 mA	
Peak Base current – Basis-Spitzenstrom		- I _{BM}	200 mA	
Peak Emitter current – Emitter-Spitzenstrom		I _{EM}	1000 mA	
Junction temperature – Sperrschichttemperatur		T _j	150°C	
Storage temperature – Lagerungstemperatur		T _S	- 65...+ 150°C	

Characteristics, T_j = 25°C**Kennwerte, T_j = 25°C**

			Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis					
- V _{CE} = 1 V, - I _C = 100 mA	BC807W	h _{FE}	100	–	600
	BC808W	h _{FE}	40	–	–
- V _{CE} = 1 V, - I _C = 500 mA	Group -16W	h _{FE}	100	160	250
	Group -25W	h _{FE}	160	250	400
	Group -40W	h _{FE}	250	400	600

¹⁾ Mounted on P.C. board with 3 mm² copper pad at each terminal
 Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt-pad) an jedem Anschluß

Characteristics, $T_j = 25^\circ\text{C}$ Kennwerte, $T_j = 25^\circ\text{C}$

	Min.	Typ.	Max.
Collector saturation voltage – Kollektor-Sättigungsspg. - $I_C = 500\text{ mA}$, - $I_B = 50\text{ mA}$ - V_{CEsat}	–	–	0.7 V
Base saturation voltage – Basis-Sättigungsspannung - $I_C = 500\text{ mA}$, - $I_B = 50\text{ mA}$ - V_{BEsat}	–	–	1.3 V
Base-Emitter voltage – Basis-Emitter-Spannung - $V_{CE} = 1\text{ V}$, - $I_C = 500\text{ mA}$ - V_{BE}	–	–	1.2 V
Collector-Base cutoff current – Kollektorreststrom $I_E = 0$, - $V_{CB} = 20\text{ V}$ - I_{CB0}	–	–	100 nA
$I_E = 0$, - $V_{CB} = 20\text{ V}$, $T_j = 150^\circ\text{C}$ - I_{CB0}	–	–	5 μA
Emitter-Base cutoff current – Emittorreststrom $I_C = 0$, - $V_{EB} = 4\text{ V}$ - I_{EB0}	–	–	100 nA
Gain-Bandwidth Product – Transitfrequenz - $V_{CE} = 5\text{ V}$, - $I_C = 10\text{ mA}$, $f = 50\text{ MHz}$ f_T	80 MHz	100 MHz	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität - $V_{CB} = 10\text{ V}$, $I_E = i_c = 0$, $f = 1\text{ MHz}$ C_{CB0}	–	10 pF	–
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft	R_{thA}		620 K/W ¹⁾
Recommended complementary NPN transistors Empfohlene komplementäre NPN-Transistoren	BC 817W / BC 818W		

Marking of available current gain groups per type	BC 807-16W = 5A	BC 807-25W = 5B	BC 807-40W = 5C
	BC 807W = 5D		
Stempelung der lieferbaren Stromverstärkungsgruppen pro Typ	BC 808-16W = 5E	BC 808-25W = 5F	BC 808-40W = 5G
	BC 808W = 5H		

¹⁾ Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluß